

## Supporting Information

# Structural stability, optical and thermoelectric properties of the layered RbSn<sub>2</sub>Br<sub>5</sub> halide synthesized using mechanochemistry

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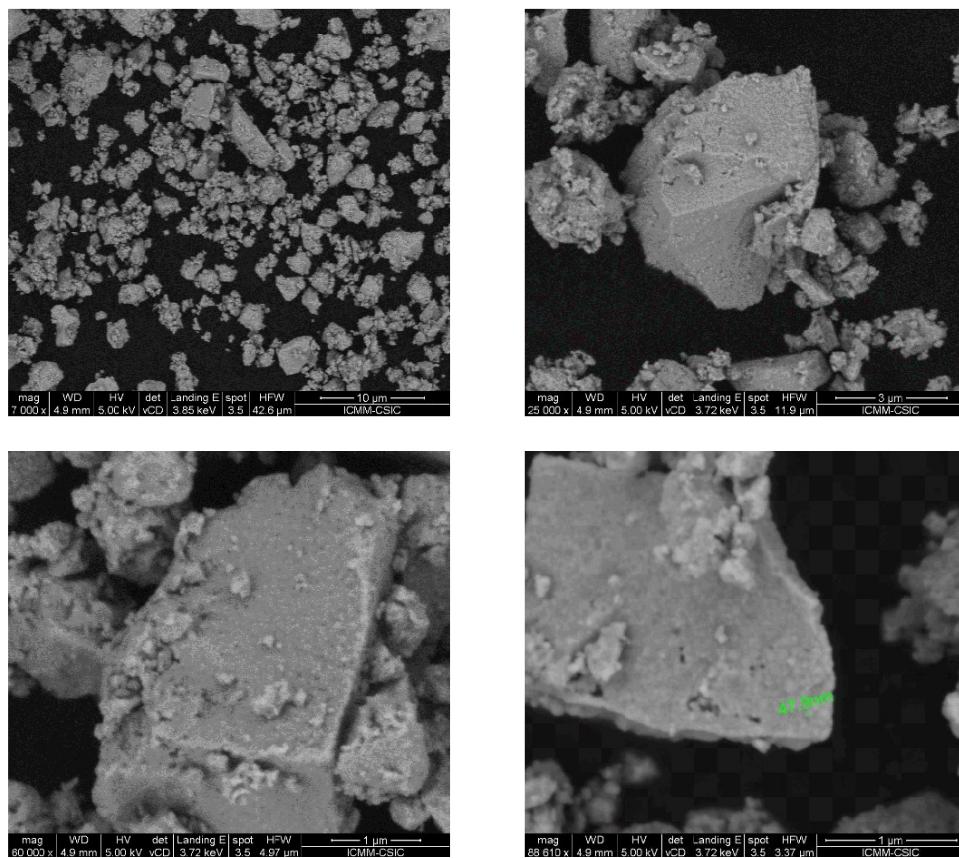
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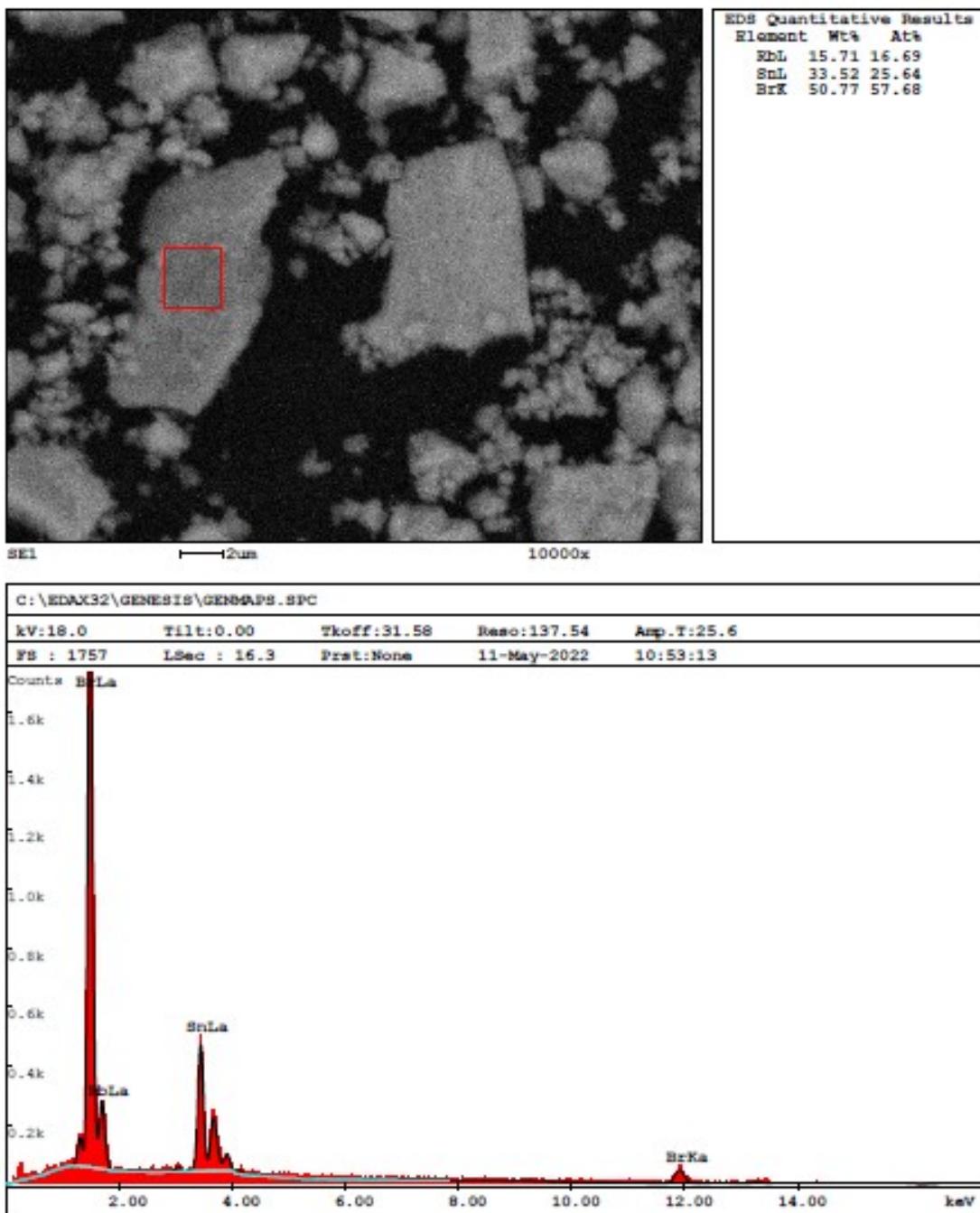
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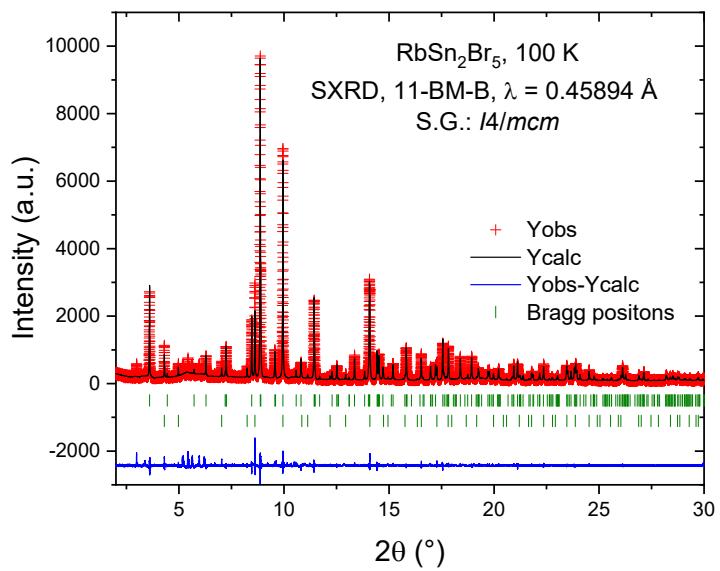
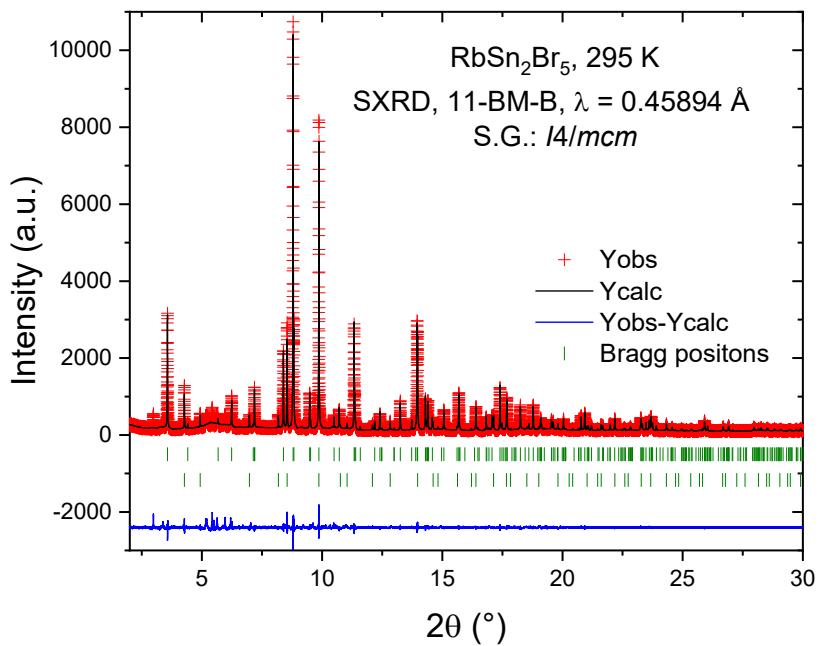
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**Figure S1:** FE-SEM images with **a)** 7,000x, **b)** 25,000x, **c)** 60,000 and **d)** 88,610x magnification.



**Figure S2.** Upper panel: SEM image where the EDX spectrum was collected, and relative contents of Rb, Sn and Br. Lower panel: typical EDX spectrum.



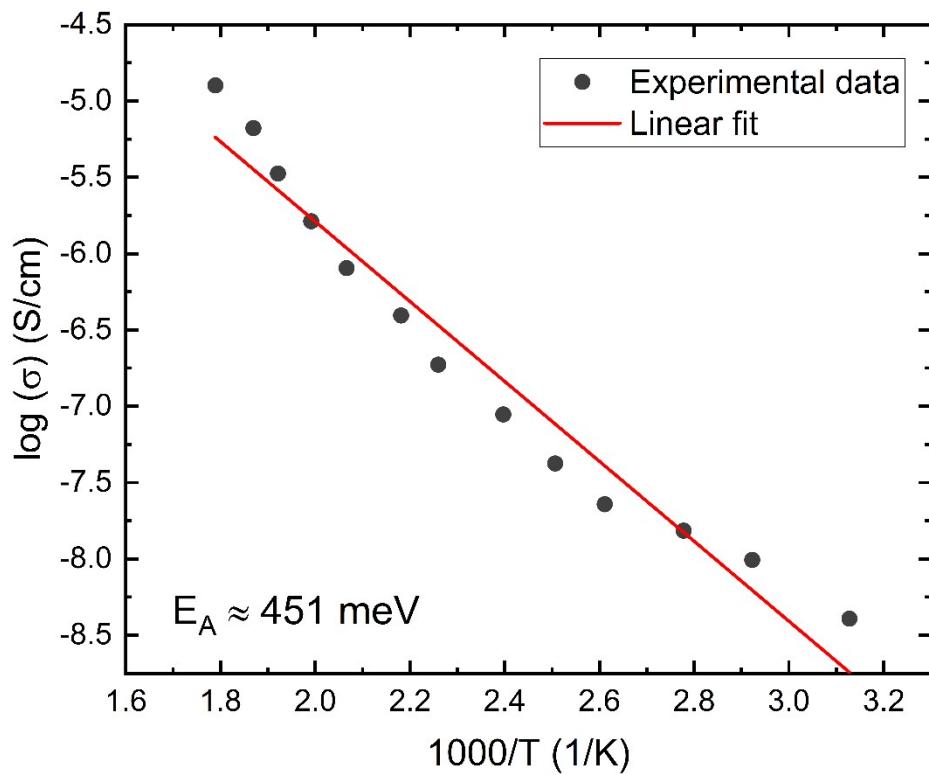
**Figure S3.** Rietveld refinements from Synchrotron X ray diffractions patterns at 295 and 100 K. The second lines of bars correspond to Rb<sub>2</sub>SnBr<sub>6</sub> (Cubic, S.G.: *Fm-3m*) phase, detected and included as impurity in the refinement.

**Table S1:** Crystallographic parameters for RbSn<sub>2</sub>Br<sub>5</sub> phase in the tetragonal system (*I4/mcm*) from SXRD data at 295 K.  $a = 8.43815(3)$  Å,  $c = 14.75126(7)$  Å and  $V = 1050.33(1)$  Å<sup>3</sup>

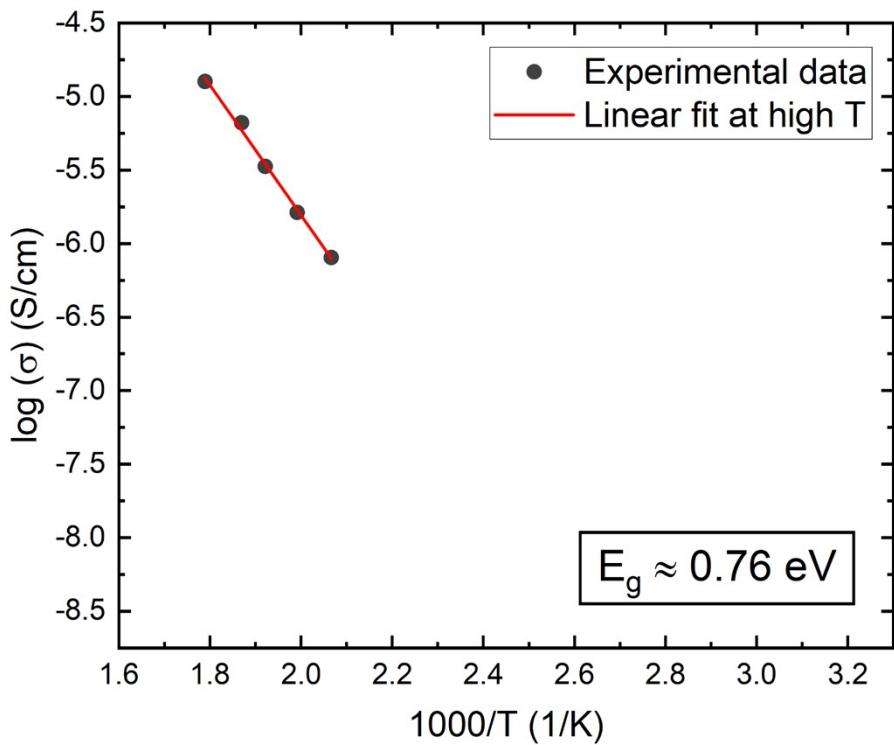
	$x$	$y$	$z$	$U_{eq}$	$f_{occ}$
<b>Rb</b>	0	0	0.25	0.031(1)	1
<b>Sn</b>	0.17769(9)	0.67769(9)	0	0.0365(6)	1
<b>Br<sub>1</sub></b>	0	0	0	0.023(1)	1
<b>Br<sub>2</sub></b>	0.16161(7)	0.66161(7)	0.36608(5)	0.0239(5)	1
<b>Anisotropic Atomic Displacement Parameters (Å<sup>2</sup>)</b>					
	U <sup>11</sup>	U <sup>22</sup>	U <sup>33</sup>	U <sup>12</sup>	U <sup>13</sup>
<b>Rb</b>	0.040(1)	0.040(1)	0.032(2)	0	0
<b>Sn</b>	0.0329(5)	0.0329(5)	0.0438(9)	-0.0042(8)	0
<b>Br<sub>1</sub></b>	0.0131(9)	0.0131(9)	0.043(2)	0	0
<b>Br<sub>2</sub></b>	0.0245(4)	0.0245(4)	0.0227(6)	0.0013(7)	-0.0033(4)
$R_p = 6.38\%$ , $R_{wp} = 8.35\%$ , $\chi^2 = 1.71$ , $R_{Bragg} = 3.55\%$ Impurity: Rb <sub>2</sub> SnBr <sub>6</sub>					

**Table S2:** Crystallographic parameters for RbSn<sub>2</sub>Br<sub>5</sub> phase in the tetragonal system (*I4/mcm*) from SXRD data at 100 K.  $a = 8.37171(4)$  Å,  $c = 14.61783(8)$  Å and  $V = 1024.36(1)$  Å<sup>3</sup>

	$x$	$y$	$z$	$U_{eq}$	$f_{occ}$
<b>Rb</b>	0	0	0.25	0.0137(9)	1
<b>Sn</b>	0.17793(9)	0.67793(9)	0	0.0152(5)	1
<b>Br<sub>1</sub></b>	0	0	0	0.0056(9)	1
<b>Br<sub>2</sub></b>	0.16104(7)	0.66104(7)	0.36451(5)	0.0099(4)	1
<b>Anisotropic Atomic Displacement Parameters (Å<sup>2</sup>)</b>					
	U <sup>11</sup>	U <sup>22</sup>	U <sup>33</sup>	U <sup>12</sup>	U <sup>13</sup>
<b>Rb</b>	0.0168(8)	0.0168(8)	0.007(1)	0.00000	0.00000
<b>Sn</b>	0.0124(4)	0.0124(4)	0.0209(7)	0.0005(7)	0.00000
<b>Br<sub>1</sub></b>	0.0042(8)	0.0042(8)	0.009(1)	0.00000	0.00000
<b>Br<sub>2</sub></b>	0.0095(4)	0.0095(4)	0.0106(5)	0.0015(6)	-0.0001(3)
$R_p = 6.80\%$ , $R_{wp} = 8.89\%$ , $\chi^2 = 2.05$ , $R_{Bragg} = 1.99\%$ Impurity: Rb <sub>2</sub> SnBr <sub>6</sub>					

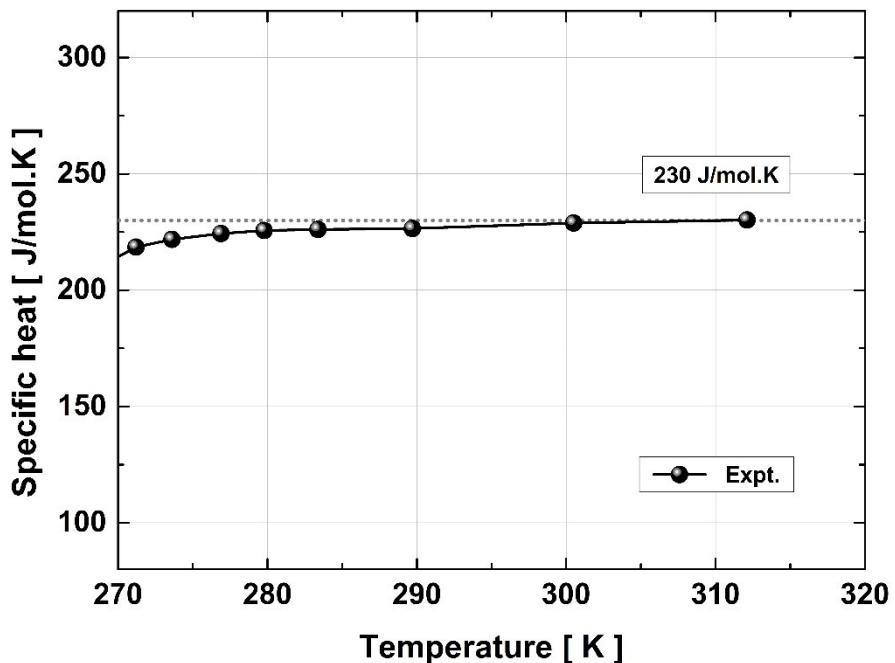


**Figure S4.** Activation energy for the carriers of the  $\text{RbSn}_2\text{Br}_5$  halide calculated from the measured electrical conductivity.



**Figure S5.** Activation energy for the carriers of the  $\text{RbSn}_2\text{Br}_5$  halide calculated from the measured electrical conductivity at high temperature. The calculated energy band gap is included in the Figure.

Compared with the experimental band gap of ~3 eV obtained from the UV-Vis spectrum, this value is significantly lower, and it is also lower than the one theoretically calculated from the structural model (~2.9 eV). This deviation can be originated by the presence of traps or defects levels in the band gap. For this reason, we can consider the value of ~3 eV offered by the UV-Vis spectrum (which agrees with the calculated one) as the most reliable result.



**Figure S6.** Experimental specific heat of  $\text{Rb}_2\text{SnBr}_6$  halide (in units of  $\text{J/mol.K}$ ) as derived from heat capacity measurements.

The experimental curve exhibited one plateau in the temperature ranges 270–320 K, converging as  $c_p \approx 230 \text{ J/mol.K}$  that is a value estimated from the thermal conductivity using the Dulong-Petit approximation.